

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1. (Previously Presented) A memory device having plural DRAM sub-arrays, each with plural array rows, comprising:
 - an address decoder for decoding an address of a memory access request and indicating which of the plural DRAM sub-arrays are referenced by the memory access request;
 - and
 - refresh circuitry, responsive to the indication of the address decoder, to refresh at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request while contemporaneously performing the memory request, wherein logically adjacent rows are placed in different sub-arrays,
 - wherein a first row is in a first sub-array and a second row is in a second sub-array, the second row being one logical row from the first row, and a third row is in the first sub-array and a fourth row is in the second sub-array, the fourth row being one logical row from the third row.
2. (Original) The memory device as claimed in claim 1, wherein the memory access request comprises a read access request.
3. (Original) The memory device as claimed in claim 2, further comprising a non-array row, external to the DRAM sub-arrays, for receiving from the DRAM sub-array referenced by the address of the read access request at least a portion of an array row corresponding to the address of the read access request.
4. (Cancel)
5. (Original) The memory device as claimed in claim 3, further comprising:

a tag register for storing at least a portion of the address of a read access request that last stored information into the non-array row; and

a comparator for signaling that the read access request may be serviced from the non-array row rather than the array row corresponding to the address of the read access request.

6. (Original) The memory device as claimed in claim 1, wherein the memory access request comprises a write access request.

7. (Original) The memory device as claimed in claim 6, further comprising a non-array row, external to the DRAM sub-arrays, for storing, prior to writing to the DRAM sub-array referenced by the address of the write access request, at least a portion of an array row corresponding to the address of the write request.

8. - 9. (Cancel)

10. (Original) The memory device as claimed in claim 1, wherein the refresh circuitry comprises a refresh counter for storing a next array row to be refreshed in at least one of the plural DRAM sub-arrays.

11. (Previously Presented) A method of refreshing a memory device having a plural DRAM sub-arrays, each with plural array rows, the method comprising:

(a) placing logically adjacent rows in different sub-arrays, wherein a first row is in a first sub-array and a second row is in a second sub-array, the second row being one logical row from the first row, and a third row is in the first sub-array and a fourth row is in the second sub-array, the fourth row being one logical row from the third row;

(b) decoding an address of a memory request;

(c) indicating which of the plural DRAM sub-arrays are referenced by the memory access request;

(d) refreshing, in response to the indicating step, at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request; and

(e) executing the memory address request,

wherein steps (d) and (e) are performed contemporaneously.

12. (Original) The method as claimed in claim 11, wherein the memory access request comprises a read access request.

13. (Original) The method as claimed in claim 11, further comprising:
receiving, into a non array row external to the plural DRAM sub-arrays and from the DRAM sub-array referenced by the address of the read access request, at least a portion of an array row corresponding to the address of the read request.

14. - 15. (Cancel)

16. (Original) The method as claimed in claim 11, wherein the memory access request comprises a write access request.

17. (Original) The method as claimed in claim 16, further comprising storing into a non-array row, external to the DRAM sub-arrays, prior to writing to the DRAM sub-array referenced by the address of the write access request, at least a portion of an array row corresponding to the address of the write request.

18. - 19. (Cancel)

20. (Original) The method as claimed in claim 11, further comprising updating a refresh counter to store a next array row to be refreshed in at least one of the plural DRAM sub-arrays.

21. - 24. (Cancel)

25. (Previously Presented) The memory device as claimed in claim 1, wherein every other logically adjacent row resides on a separate sub-array.

26. (Previously Presented) The memory device as claimed in claim 1, wherein even numbered rows and odd numbered rows reside on separate sub-arrays.

27. (Previously Presented) A memory device having plural DRAM sub-arrays, each with plural array rows, comprising:

an address decoder for decoding an address of a memory access request and indicating which of the plural DRAM sub-arrays are referenced by the memory access request; and

refresh circuitry, responsive to the indication of the address decoder, to refresh at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request while contemporaneously performing the memory request, wherein logically adjacent rows are placed in different sub-arrays,

wherein each row of a first sub-array is L rows higher in logical memory than each corresponding row of a second sub-array, wherein L is an integer less than the maximum number of rows in a sub-array.

28. (Previously Presented) A memory device having plural DRAM sub-arrays, each with plural array rows, comprising:

an address decoder for decoding an address of a memory access request and indicating which of the plural DRAM sub-arrays are referenced by the memory access request; and

refresh circuitry, responsive to the indication of the address decoder, to refresh at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request while contemporaneously performing the memory request, wherein logically adjacent rows are placed in different sub-arrays, and the logically adjacent rows in different sub-arrays comprise rows other than the last and first rows of consecutive sub-arrays.

29. (Previously Presented) A memory device having plural DRAM sub-arrays, each with plural array rows, comprising:

an address decoder for decoding an address of a memory access request and indicating which of the plural DRAM sub-arrays are referenced by the memory access request; and

refresh circuitry, responsive to the indication of the address decoder, to refresh at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request while contemporaneously performing the memory request, wherein logically adjacent rows are placed in different sub-arrays;

wherein a first row is in physical memory row N of a first sub-array and a second row is in physical memory row M of a second sub-array, wherein the second row is absolutely higher in logical memory than the first row and the second row is $X+(M-N)$ logical rows from the first row, wherein N and M are integers from 1 to K and X is an integer greater than -K and less than K, wherein K is the maximum number of rows in a sub-array.

30. (Previously Presented) A method of refreshing a memory device having a plural DRAM sub-arrays, each with plural array rows, the method comprising:

(a) placing logically adjacent rows in different sub-arrays, and the logically adjacent rows in different sub-arrays comprise rows other than the last and first rows of consecutive sub-arrays;

(b) decoding an address of a memory request;

(c) indicating which of the plural DRAM sub-arrays are referenced by the memory access request;

(d) refreshing, in response to the indicating step, at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request; and

(e) executing the memory address request,

wherein steps (d) and (e) are performed contemporaneously.

31. (Previously Presented) A method of refreshing a memory device having a plural DRAM sub-arrays, each with plural array rows, the method comprising:

(a) placing logically adjacent rows in different sub-arrays, wherein a first row is in physical memory row N of a first sub-array and a second row is in physical memory row M of a second sub-array, wherein the second row is absolutely higher in logical memory than the first row and the second row is $X+(M-N)$ logical rows from the first row, wherein N and M are

integers from 1 to K and X is an integer greater than -K and less than K, wherein K is the maximum number of rows in a sub-array;

(b) decoding an address of a memory request;

(c) indicating which of the plural DRAM sub-arrays are referenced by the memory access request;

(d) refreshing, in response to the indicating step, at least one array row of at least one of the plural DRAM sub-arrays not referenced by the memory access request; and

(e) executing the memory address request,

wherein steps (d) and (e) are performed contemporaneously.